

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re patent application of

Norikatsu Koide et al.

Serial No.: 09/711,908

Group Art Unit: 2814

Filed: November 15, 2000

Examiner: Louie, Wai Sing

For: METHODS FOR MANUFACTURING A LIGHT-EMITTING DEVICE

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

REQUEST FOR CONSIDERATION OF
INFORMATION DISCLOSURE STATEMENT

Sir:

Applicant respectfully requests that the Information Disclosure Statement submitted and filed on November 15, 2000, be officially considered of record. Attached is a copy of the Form PTO-1449 filed on November 15, 2000, as well as a copy of the date-stamped postcard. Applicant respectfully requests that the Examiner officially acknowledge the disclosed information and promptly return the initialed Form PTO-1449.

Respectfully submitted,

Dated: 12/11/03

Peter A. Balnave
Peter A. Balnave
Reg. No. 46,199

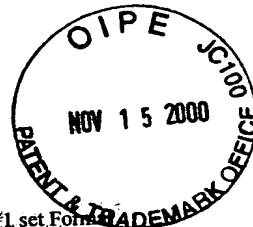
McGinn & Gibb, PLLC
8321 Old Courthouse Road
Suite 200
Vienna, Virginia 22182-3817
(703) 761-4100
Customer Number: 21254



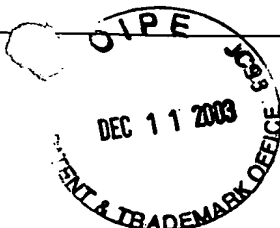
PAT-103-8/99 PTO REC-1 INDICATED ITEMS Atty. PWG/GRT
Appln. No: 0 / Date 11/15/2000
Inventor(s): KOIDE et al. CH# 51273
Title: Methods for Manufacturing a Light-Emitting Device M# 268415

ENCLOSED:

- ☒ Preliminary Amendment
- ☐ No. of Pages Abstract
- # 17 No. of Pages Spec and Claims
- # 12 No. of numbered Claims only
- ☒ Declaration (2 #pgs)
- ☒ Assignment ☒ Cover Sheet
- # No. of Priority Documents
- # 2 No. Sheets Drawings (Fig(s) 1 to 2+) ☒ 1 set Form
- ☐ IDS Letter ☐ citing App: ☐ Foreign sch rept/OA
- ☒ PTO-1449 ☐ cited docs.
- \$ 750.00 Fee (Check)
- Other:



CURRENT DUE DATE: November 15, 2000



Atty. Dkt. No.	M#	Cl. nt Ref.
	268415	T36-127889 M/KOH

**INFORMATION DISCLOSURE STATEMENT
BY APPLICANT**

Applicant: KOIDE et al.	
Appln. No.: Continuation of Appln. No. 08/925,323	
Filing Date: November 15, 2000	
Examiner: J. JACKSON	Group Art Unit: 2815

Date: November 15, 2000

Page 1 of 1

U.S. PATENT DOCUMENTS

Examiner's Initials*	Document Number	Date MM/YYYY	Name (Family Name of First Inventor)	Class	Sub Class	Filing Date (if appropriate)
	AR 5,929,466	07/1999	OHBA			
	BR 5,877,558	03/1999	NAKAMURA et al.			
	CR 5,760,945	06/1998	COLEMAN			
	DR 5,656,823	08/1997	KRUANGAM			
	ER 5,502,316	03/1996	KISH et al.			
	FR 5,466,950	11/1995	SUGAWARA et al.			
	GR 5,641,682	06/1997	NIRE et al.			
	HR 5,592,501	01/1997	EDMOND et al.			
	IR					
	JR					
	KR					
	LR					
	MR					
	NR					

FOREIGN PATENT DOCUMENTS

		Document Number	Date MM/YYYY	Country	Inventor Name		English Abstract		Translation Readily Available	
							Enclosed	No	Enclos	No
	OR									
	PR									
	QR									
	RR									
	SR									
	TR									
	UR									

OTHER (Including in this order Author, Title, Periodical Name, Date, Pertinent Pages, etc.)

VR	Nakamura, "Growth of $\text{In}_x\text{Ga}_{1-x}\text{N}$ Compound Semiconductors and High-Power InGAN/AlGaN Double Heterostructure Violet-Light-Emitting Diodes," Microelectronics Journal, 1994, Vol. 25, pp. 651-659			
WR	Osamura et al., "Preparation and Optical Properties of $\text{Ga}_{1-x}\text{In}_x\text{N}$ Thin Films," Journal of Applied Physics, August 1975, Vol. 46, No. 8, pp. 3432-3437			
XR	Nakamura et al., "P-GaN/N-InGaN/N-GaN Double-Heterostructure Blue-Light-Emitting Diodes," Japanese Journal of Applied Physics, 1993, Vol. 32, pp. L8-L11			
YR				
ZR				
AAR				

Examiner	Date Considered:
*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.	